Resistive Switching. From Fundamentals of Nanoionic Redox Processes to Memristive Device Applications

Description:
With its comprehensive coverage, this reference introduces readers to the wide topic of resistance switching, providing the knowledge, tools, and methods needed to understand, characterize and apply resistive switching memories.

Starting with those materials that display resistive switching behavior, the book explains the basics of resistive switching as well as switching mechanisms and models. An in-depth discussion of memory reliability is followed by chapters on memory cell structures and architectures, while a section on logic gates rounds off the text.

An invaluable self-contained book for materials scientists, electrical engineers and physicists dealing with memory research and development.

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